

Too Hot To Test February 9 - 11, 2021

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February 10, 2021

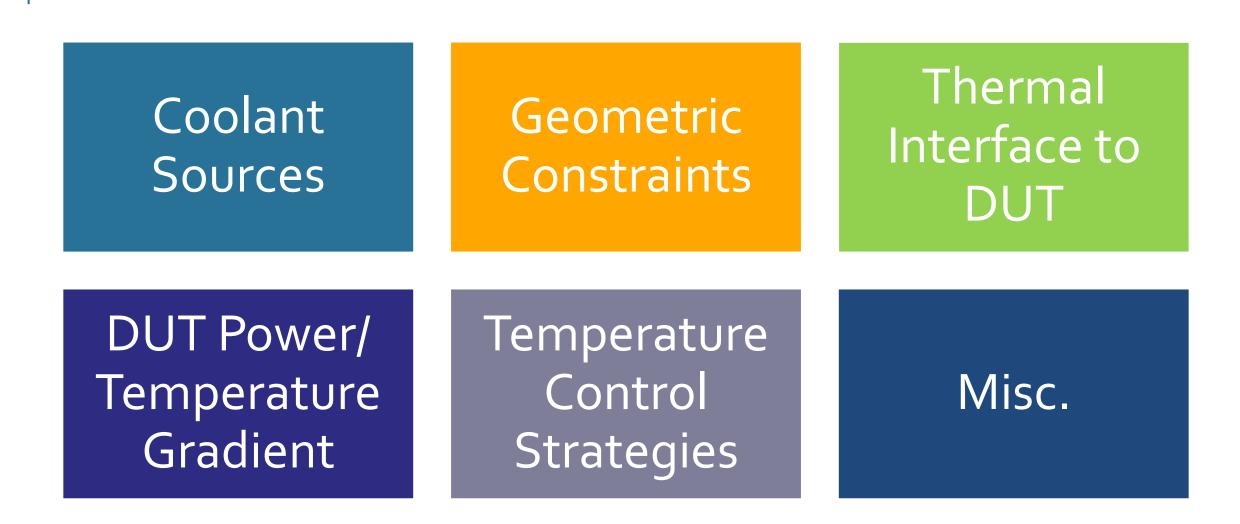
Thermal Control Challenges of High Power DUTs during Test

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Overview – Factors to be Addressed





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Coolant Sources

Air

- Inexpensive and benign
- Practical at hot setpoints only
- Practical for limited power capacity
- High performance applications noisy



Liquid

- Higher thermal capacitance → better performance
- Best fluids are either flammable or limited in temperature range
- Water
 - Great performance
 - Limited from o°C to 100°C (can extend somewhat by mixing glycols)
 - Requires leak tolerant design
- HFE
 - Lower performance
 - No fluid version is optimal over entire needed temperature range
- Thermal losses from cooling source to DUT control location



Phase Change

LN₂

- Can be used to extremely low temperatures
- Low thermal capacity, consumption costly, and safety concerns
- Resistance from customers due to various reasons

Refrigeration

- High thermal capacity
- Most effective with evaporator at test site (not through secondary medium)
- Routing supply and return lines complex
- Complexity and cost increase significantly below -40°C
 - Multi-stage
 - Oil return

Water

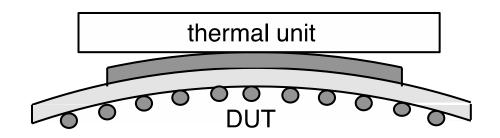
- At high temperature setpoints
 - Great performance, benign material



Geometric Constraints - Flatness

Large Device Area

- Usually implies lower power density → easier to control
- DUT not flat
 - Larger thermal gaps
 - Poorer control
 - Convex curvature is typical
 - Larger thermal gap
 - less risk to damage bare die edges
 - Sometimes can take advantage of DUT flexibility to "flatten"
 - Significant performance improvement
 - Small risk of permanent "damage" to DUT
- Many device and package styles
 - Requires custom thermal unit designs



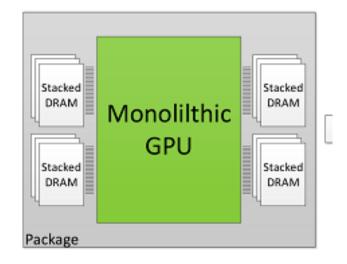


Geometric Constraints

Multichip Applications

- Single high-power device, multiple low power
- Contact surface on devices may not be coplanar
- High power device
 - Needs tight temperature control
- All other devices
 - Temperature control not as critical
 - Prevent exceeding maximum temperature
- Optimize TU to control high power device
- Control low power devices with compliant TIM





Source: NVIDIA MCM-GPU: Multi-Chip-Module GPUs for Continued Performance Scalability. June 26, 2017

https://research.nvidia.com/publication/2017-06_MCM-GPU%3A-Multi-Chip-Module-GPUs

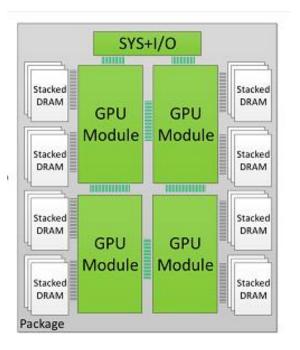


Geometric Constraints

Multichip Applications

- Multiple high-power devices, multiple low power
- Requires that contact surfaces for high power chips be coplanar
- If not:
 - Multiple thermal units or control zones
 - Technically feasible but costly
 - High performance TIM
- Increasing requests to test multichip bare die
 - No lid \rightarrow lower thermal resistance path (a plus)
 - Non coplanar → higher thermal resistance path (a minus)





Source: NVIDIA MCM-GPU: Multi-Chip-Module GPUs for Continued Performance Scalability. June 26, 2017

https://research.nvidia.com/publication/2017-06_MCM-GPU%3A-Multi-Chip-Module-GPUs

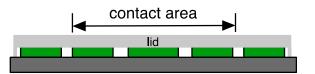


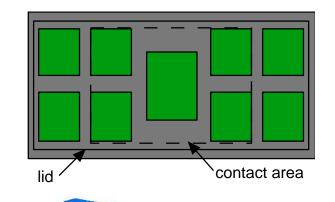
Geometric Constraints

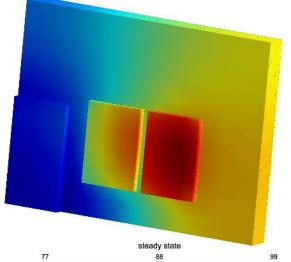
Large Lidded Multichip Devices

- Contact surface is planar (Yay!)
- Still a testing challenge
- Assume
 - Power density is equal on all devices pictured
 - Thermal unit does not contact entire device
- Quarter symmetry analysis → large temperature gradient
- Large device requires large thermal unit

• Many different sizes on the market (no standard)









Thermal Interface Materials (TIM)

Requirements

- Low thermal resistance
- Highly compliant
- Reusable to many cycles
- Repeatable performance
- No residue or easily cleaned
- Easily refurbished

Thermal Interface to DUT



TIM Examples

Helium

- Inert
- Substantially better than a dry interface
- High consumption cost
- Global shortage

Malleable Metal

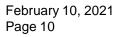
- Usually indium
- Good conductivity
- Subject to oxidation (unless Au)
- Creep over time
- Limited life
- Indium melts at ~150°C

Liquid Metal Alloy

- Excellent conductivity and compliance
- Oxidation
- Needs containment mechanism
- Limited temperature range
- May attack other metals (gallium)







TIM Examples

Volatile Liquid

- Good conductivity and compliance
- Limited temperature range
- Possible application, removal, and cleaning issues

Elastomeric

- Bulk conductivity may be good
- Good compliance
- Compression pressure may be limited
- Subject to creep
- Typically needs additional treatment or material to easily release from DUT
 - \rightarrow Additional thermal

resist



Graphite/Carbon-based

- Excellent bulk conductivity but may be directional
- Usually not very compliant
- Fairly robust
- Only as good as thermal contact resistance to DUT and thermal unit





Practical Good Performing TIM is a Critical Need!

- In high power applications, major thermal resistance is between DUT and thermal unit
- □ Currently TIM when used is limited to a particular type of application
- □ Market for TIM used in test is small → limited supplier competition

Thermal Interface to DUT



Manufacturing Test Environment

Need procedure to test TIM performance in manufacturing test environment



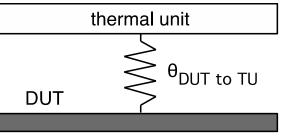
- Typical method is steady state
 - Well proven direct method
 - Not an option if DUT thermal sensor is not available
 - Applying known amount of power not trivial
 - For lidded devices, lid to DUT thermal resistance variation may be greater than resolution needed for measuring the resistance of the TIM between the lid and heater

Thermal Interface to DUT



Temperature Gradient

- □ For high power devices one must minimize thermal resistance from the thermal unit to the DUT, θDUT to TU
- When θDUT to TU approaches the DUT in plane resistance θDUT in plane or becomes less → DUT can develop significant temperature gradients
- Temperature gradients proportional to power dissipated
- Important to understand gradient
 - Location of temperature sensor important
 - One application controlled DUT at sensor location well
 - Gradient caused solder balls to melt
- □ See example on next slide
 - Center sensor poor choice for control

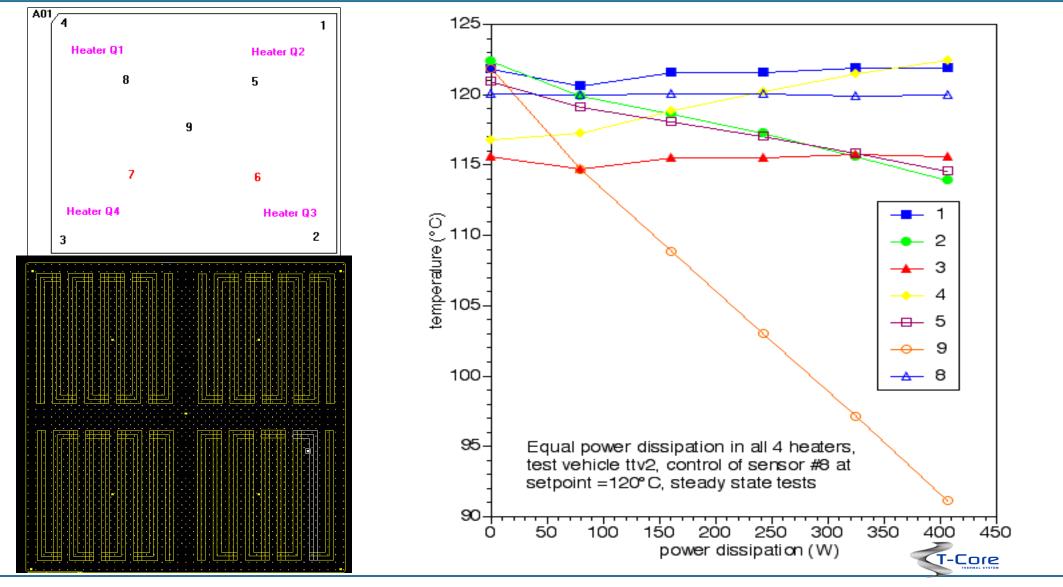




DUT Power/ Temperature Gradient



Center Sensor Poor Choice for Control





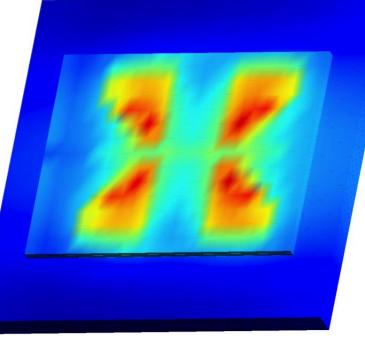
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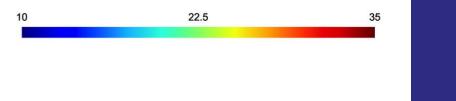
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Power Dissipation on most Devices not Uniformly Distributed

Device shown is 4 core processor

- DUT power concentrated near cores
- Hottest near cores





DUT Power/ Temperature Gradient

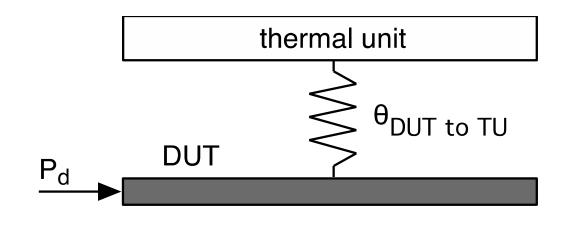


DUT Power vs. Time

Referencing the simplified figure shown



- For constant DUT power Pd thermal unit required temperature is also constant
- Slow or small changes of Pd require simple changes of thermal unit temperature
- Large or fast changes of Pd require more difficult changes of thermal unit temperature
 - ➤ Lagging changes of required thermal unit temperature can result in significant DUT temperature rise
 → increased DUT power (higher leakage current) → thermal runaway



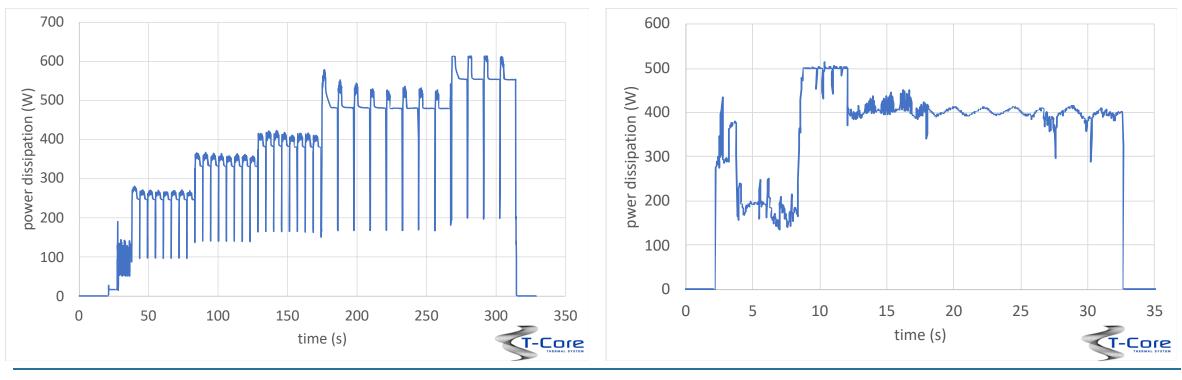
DUT Power/ Temperature Gradient



Importance of DUT Power Change Magnitude

DUT power change magnitude more important than absolute power magnitude

- Burn-in power dissipation fairly constant \rightarrow easy to control
- Functional test & SLT power varies \rightarrow harder to control
- Figures below show two DUT power dissipation profiles





Temperature Control Modes

□ HTF – control temperature of thermal unit

- Constant temperature of thermal unit
 - > DUT temperature = (Pd * θ DUT to TU) + temperature of thermal unit
 - > May be acceptable if θ DUT to TU is small : very good TIM!
- Change temperature of thermal unit based on anticipated power profile (open loop)
 - > Can't use for non-constant power profiles (example: test with branching)

□ HTF-PF - control temperature of thermal unit as a function of measured DUT power

- Called power following mode
- Fast dynamic control to get DUT temperature to desired set point temperature
- Sensitive to varying θDUT to TU
- Dynamic-PF control temperature of thermal unit as a function of measured DUT power changes
 - Dynamic power following
 - Used with in conjunction with other control modes





Direct Temperature Feedback (DTF)

□ Control with DUT temperature sensor(s) present

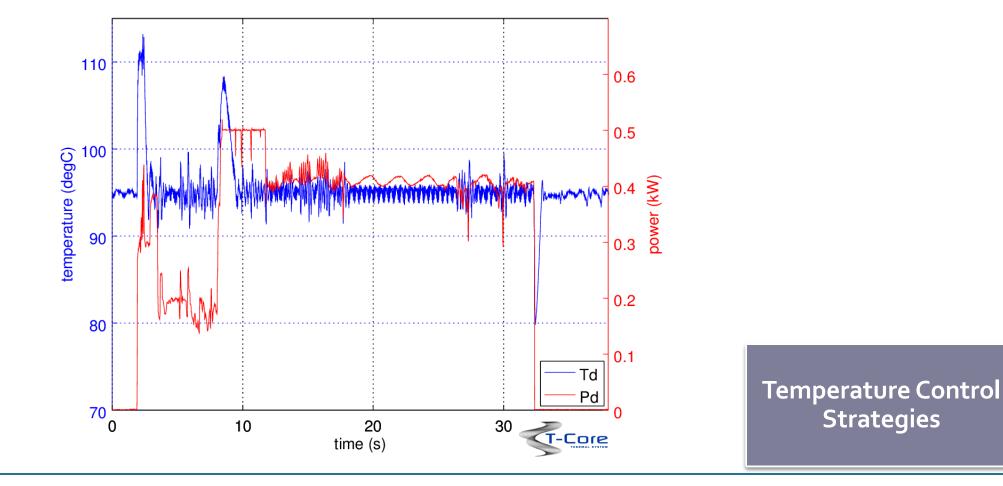
- Typically diode or RTD on chip
- Theoretically more accurate and more stable
- Sensor output varies with manufacturing tolerances
 - > In-situ calibration with heater eliminates error
 - > Use saturation current cancellation technique
- Sensor location may not be optimal
 - > Non uniform power dissipation
 - > Large temperature gradients across chip
- Digital sensors beginning to appear (must be provided at fast rate)
- Common feedback from tester (not useable)
 - Access available between subtests only
 - No feedback without DUT power
- Strategies exist to use multiple sensor combinations
 - > Multichip modules may change sensors when powering different chips

Temperature Control Strategies



Direct Temperature Feedback (DTF)

□ Liquid cooled application, DUT temperature Td vs. DUT power Pd





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Extrapolated Temperature Feedback (ETF)

□ Some devices do not allow device or power feedback

• Power feedback may only be partial

Calculate DUT Temperature based on thermal head dynamics only

- Multiple sensors in thermal unit
- Not as robust as PF
- □ Requires low θ DUT to TU \rightarrow (excellent TIM!)
 - Cannot extrapolate too far

Contains dynamic term

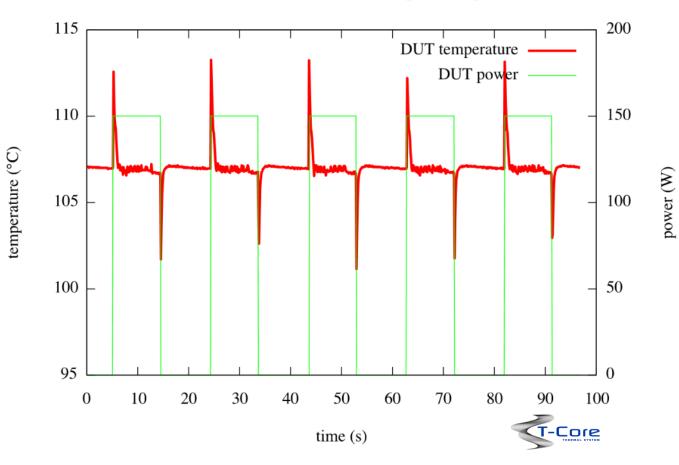
Temperature Control Strategies



Extrapolated Temperature Feedback (ETF)

- □ Air cooled with thermal test vehicle
- **Controlled with ETF**
- Monitored with thermal sensor

Tcore air TU, ETF, unlidded, 150.2W pulses, Tsp=107°C



Much Easier Temperature Control at Hot Setpoints vs Cold

- □ Fortunately, power dissipation is typically much lower at cold than hot
- Larger difference between setpoint and cold source temperatures allows high heat transfer rates
- □ -40°C often considered a practical limit
- □ As cold source temperatures decrease, complexity and costs go up exponentially
 - Multi-stage compressor
 - LN2
 - Condensation control
- Secondary paths to ambient
 - Helps control at hot
 - Adds additional burden at cold



Other comments

□ Absolute power not the best measure of temperature control difficulty

- Dominant factors:
 - DUT power dissipation density
 - Magnitude of DUT power dissipation changes during test
 - Test temperature setpoint
 - DUT package resistance
 - Device geometry
- Application requirement vary greatly
- Initial requirements for application often erroneous
 - Sometimes to stringent and sometimes too lax

□ New temperature control candidates (such mobile or automotive applications)

- Newest devices dissipate significant amount of power
- New territory for these test engineers





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